

Cypress Semiconductor Product Qualification Report

QTP# 030702 VERSION 3.0
March 2008

PSoC™ Mixed Signal Array Family S4AD-5CTI Technology, Fab 2 CTI	
CY8C27143	PSoC™ Mixed Signal Array
CY8C27243	PSoC™ Mixed Signal Array
CY8C27443	PSoC™ Mixed Signal Array
CY8C27543	PSoC™ Mixed Signal Array
CY8C27643	PSoC™ Mixed Signal Array

CYPRESS TECHNICAL CONTACT FOR QUALIFICATION DATA:

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PRODUCT QUALIFICATION HISTORY

Qual Report	Description of Qualification Purpose	Date Comp
010702	New Technology S4AD-5 / New Product, Programmable Clock Generator, CY2414ZC, product family and bond option.	Apr 01
003605	Technology Derivative S4D-5 /New Neuron Devices, CY7C53150 and CY7C53120	Jul 01
030702	New PSoC™ CY8C27xxx device and product family in smaller die	Nov 03
043105	5-Layer Mask change for ALL CY8C27xxxB product family	Nov 04
074504	3 Layer Mask change (M1, Via, and M2) for PSoC Diamond Device (CY8C27x43)	Jan 08

PRODUCT DESCRIPTION (for qualification)			
Qualification Purpose: New device CY8C27xxx and product family in S4D-5CTI Technology in Fab 2			
Marketing Part #:	CY8C27143, CY8C27243, CY8C27443, CY8C27543, CY8C27643		
Device Description:	3.3V and 5V, Industrial, available in 8/20/28/48 lead PDIP, 20/28-lead SOIC, 20/28/48-lead SSOP and 44-lead TQFP package respectively.		
Cypress Division:	Cypress Microsystems Inc Subsidiary– (CMS) WA		
Overall Die (or Mask) REV Level (pre-requisite for qualification):			Rev. B
SONOS Flash:	16 Kbytes	SRAM:	256 bytes
What ID markings on Die:	8C27002		

TECHNOLOGY/FAB PROCESS DESCRIPTION S4AD-5CTI			
Number of Metal Layers:	2	Metal Composition:	Metal 1: 500A Ti/6,000A Al 0.5% Cu /1,200A TiW Metal 2: 500A Ti/8,000A Al 0.5% Cu/300A TiW
Passivation Type and Materials:	3,000A TEOS / 6,000A Si ₃ N ₄		
Free Phosphorus contents in top glass layer (%):	0%		
Number of Transistors in Device:	600,000		
Number of Gates in Device	100,000		
Generic Process Technology/Design Rule (-drawn):	1Poly/2Metal, 0.35 μm		
Gate Oxide Material/Thickness (MOS):	SiO ₂ / 110Å		
Name/Location of Die Fab (prime) Facility:	Cypress Semiconductor - Round Rock, TX (CTI)		
Die Fab Line ID/Wafer Process ID:	Fab2 SONOS, S4AD-5 CTI		

PACKAGE AVAILABILITY

PACKAGE	ASSEMBLY/TEST SITE FACILITY
20/28-lead PDIP	IDNS-O
20/28-lead SOIC	CML-R
20/28-lead SSOP	OSE-T, PHIL-M, CML-RA
48/56-lead SSOP	CML-R
48-lead MLF	SEUOL-L
44-pin TQFP	CML-R

Note: Package Qualification details available upon request.

MAJOR PACKAGE INFORMATION USED IN THIS QUALIFICATION	
Package Designation:	SP28
Package Outline, Type, or Name:	28-Lead Shrunk Samll Outline Packages (SSOP)
Mold Compound Name/Manufacturer:	Hitachi CeI9220HF
Mold Compound Flammability Rating:	V-O per UL94
Oxygen Rating Index:	>28%
Lead Frame Material:	Copper
Lead Finish, Composition / Thickness:	Sn Matte (100% Sn)
Die Backside Preparation Method/Metallization:	N/A
Die Separation Method:	100% Saw
Die Attach Supplier:	Ablestik
Die Attach Material:	8340
Bond Diagram Designation:	10-05762
Wire Bond Method:	Thermosonic
Wire Material/Size:	Au, 1.0mil
Thermal Resistance Theta JA °C/W:	95°C/W
Package Cross Section Yes/No:	N/A
Assembly Process Flow:	49-35026M
Name/Location of Assembly (prime) facility:	OSE-Taiwan (T)

ELECTRICAL TEST / FINISH DESCRIPTION	
Test Location:	Cypress Philippines (CML-R)
Fault Coverage:	100%

Note: Please contact a Cypress Representative for the availability of other packages.

RELIABILITY TESTS PERFORMED PER SPECIFICATION REQUIREMENT

Stress/Test	Test Condition (Temp/Bias)	Result P/F
High Temperature Operating Life Early Failure Rate	Dynamic Operating Condition, Vcc Max=5.75V, 125°C Dynamic Operating Condition, Vcc Max=5.75V, 150°C	P
High Temperature Operating Life Latent Failure Rate	Dynamic Operating Condition, Vcc Max=5.75V, 125°C	P
Temperature Cycle	MIL-STD-883C, Method 1010, Condition C, -65°C to 150°C Precondition: JESD22 Moisture Sensitivity MSL 3 192 Hrs., 30°C/60%RH+3IR-Reflow, 235°C+5, -0°C Precondition: JESD22 Moisture Sensitivity MSL 1 168 Hrs, 85°C/85%RH+3IR-Reflow, 235°C+5, -0°C	P
Pressure Cooker	121°C, 100%RH MIL-STD-883C, Method 1010, Condition C, -65°C to 150°C Precondition: JESD22 Moisture Sensitivity MSL 3 192 Hrs., 30°C/60%RH+3IR-Reflow, 235°C+5, -0°C Precondition: JESD22 Moisture Sensitivity MSL 1 168 Hrs, 85°C/85%RH+3IR-Reflow, 235°C+5, -0°C	P
High Accelerated Saturation Test (HAST)	130°C, 5.5V, 85%RH Precondition: JESD22 Moisture Sensitivity MSL 3 192 Hrs., 30°C/60%RH+3IR-Reflow, 235°C+5, -0°C 130°C, 3.63V, 85%RH Precondition: JESD22 Moisture Sensitivity MSL 1 168 Hrs, 85°C/85%RH+3IR-Reflow, 235°C+5, -0°C	P
Data Retention	150°C ± 5°C no bias	P
High Temperature Steady State Life	150°C, 363V, Vcc Max	P
Electrostatic Discharge Human Body Model (ESD-HMB)	2,200V, 2,000V MIL-STD-883, Method 3015.7	P
Electrostatic Discharge Charge Device Model (ESD-CDM)	500V Cypress Spec. 25-00020	P
Age Bond Strength	MIL-STD-883C, Method 2011	P
Acoustic Microscopy	Cypress Spec. 25-00104	P
Low Temperature Operating Life	-30C, 4.3V, 8MHZ	P
Dynamic Latchup Sensitivity	Cypress Spec. 01-00081	P
Static Latchup Sensitivity	125°C, ± 300mA In accordance with JEDEC 17. Cypress Spec. 01-00081	P

RELIABILITY FAILURE RATE SUMMARY

Stress/Test	Device Tested/ Device Hours	# Fails	Activation Energy	Thermal ³ A.F	Failure Rate
High Temperature Operating Life Early Failure Rate	1,605 Devices (043105)	0	N/A	N/A	0 PPM
High Temperature Operating Life ^{1,2} Long Term Failure Rate	593,000 DHRs (030702)	0	0.7	55	28 FITs

¹ Assuming an ambient temperature of 55°C and a junction temperature rise of 15°C.

² Chi-squared 60% estimations used to calculate the failure rate.

³ Thermal Acceleration Factor is calculated from the Arrhenius equation

$$AF = \exp \left[\frac{E_A}{k} \left[\frac{1}{T_2} - \frac{1}{T_1} \right] \right]$$

where:

E_A = The Activation Energy of the defect mechanism.

k = Boltzmann's constant = 8.62×10^{-5} eV/Kelvin.

T_1 is the junction temperature of the device under stress and T_2 is the junction temperature of the device at use conditions.

Reliability Test Data

QTP #: 010702

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ACOUSTIC-MSL1							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	COMP	15	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	COMP	15	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	COMP	15	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 150C, 3.8V, Vcc Max							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	48	1005	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	48	1004	1	NON VISUAL
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	48	1005	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 150C, 3.8V, Vcc Max							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	80	120	0	
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	500	120	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	80	120	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	500	120	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	80	120	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	500	120	0	
STRESS: AGE BOND STRENGTH							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	COMP	15	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	COMP	15	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	COMP	15	0	
STRESS: DYNAMIC LATCH-UP TESTING, 11.5V							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	COMP	3	0	
STRESS: LOW TEMPERATURE OPERATING LIFE, -30C, 4.3V							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	500	48	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	COMP	9	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	COMP	9	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	COMP	9	0	

Reliability Test Data

QTP #: 010702

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: STATIC LATCH-UP TESTING, 125C, 10V, ±300mA							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	COMP	3	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	COMP	3	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	COMP	3	0	
STRESS: HI-ACCEL SATURATION TEST, 130C, 85%RH, 3.63V, PRE COND 168 HR 85C/85%RH, MSL1							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	128	50	0	
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	256	50	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	128	48	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	128	48	0	
STRESS: HIGH TEMP STEADY STATE LIFE TEST, 150C, 3.63V							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	80	80	0	
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	168	80	0	
STRESS: ENDURANCE TEST							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	COMP	45	0	
STRESS: DATA RETENTION, PLASTIC, 150C							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	168	80	0	
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	552	80	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	168	80	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	552	80	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	168	80	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	552	80	0	
STRESS: PRESSURE COOKER TEST, 121C, 100%RH, PRE COND 168 HR 85C/85%RH, MSL1							
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	168	50	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	168	49	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	168	51	0	

Reliability Test Data

QTP #: 010702

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
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STRESS: TC COND. C -65C TO 150C, PRECONDITION 168 HRS 85C/85%RH, MSL1

CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	300	50	0	
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	500	50	0	
CY2414ZC (7C841400A)	2101502	610106170/1/2	TAIWN-T	1000	50	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	300	50	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	500	50	0	
CY2414ZC (7C841400A)	2052404	610106173/4/5	TAIWN-T	1000	50	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	300	50	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	500	50	0	
CY2414ZC (7C841400A)	2103764	610106176/7/8	TAIWN-T	1000	49	0	

Reliability Test Data

QTP #: 003605

Device	Fab Lot #	Assy Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ACOUSTIC-MSL3							
CY7C53150-AI (7C53150A)	2104858	610109389/90	TAIWN-G	COMP	15	0	
CY7C53150-AI(7C53150B)	2110601	610115306	TAIWN-G	COMP	15	0	
CY7C53150-AI (7C53150B)	2113874	340100160/1	TAIWN-G	COMP	15	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 150C, 5.75V, Vcc Max							
CY7C53120-SI (7C53120B)	2110601	610119962	CSPI-R	80	394	0	
CY7C53120-SI (7C53120B)	2113874	610119334	CSPI-R	80	591	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 125C, 5.75V, Vcc Max							
CY7C53120-SI (7C53120B)	2110601	610119962	CSPI-R	96	609	1	MISSING LICON
CY7C53120-SI (7C53120B)	2113874	610119334/7707	CSPI-R	96	414	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 150C, 5.75V, Vcc Max							
CY7C53120-SI (7C53120B)	2110601	610119962	CSPI-R	197	393	0	
CY7C53120-SI (7C53120B)	2110601	610119962	CSPI-R	500	393	0	
CY7C53120-SI (7C53120B)	2113874	610119334	CSPI-R	197	400	1	UNKNOWN
CY7C53120-SI (7C53120B)	2113874	610119334	CSPI-R	500	399	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	COMP	9	0	
STRESS: HI-ACCEL SATURATION TEST, 130C, 85%RH, 5.5V, PRE COND 192 Hrs., 30°C/60%RH, MSL3							
CY7C53150-AI (7C53150A)	2104858	610109389/90	TAIWN-G	128	48	0	
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	128	46	0	
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	256	46	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2,000V							
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	COMP	9	0	
STRESS: STATIC LATCH-UP TESTING, 125C, 12V, ±300mA							
CY7C53150-AI (7C53150A)	2104858	610109389/90	TAIWN-G	COMP	3	0	
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	COMP	3	0	
STRESS: ENDURANCE TEST, -25C/+85							
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	1000	48	0	

Reliability Test Data

QTP #: 003605

<i>Device</i>	<i>Fab Lot #</i>	<i>Assy Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
STRESS: DATA RETENTION, PLASTIC, 150C							
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	500	266	0	
CY7C53150-AI (7C53150B)	2113874	340100160/1	TAIWN-G	500	266	0	
STRESS: PRESSURE COOKER TEST, 121C, 100%RH, PRE COND 192 HR 30°C/60%RH, MSL3							
CY7C53150-AI (7C53150A)	2104858	610109389/90	TAIWN-G	168	50	0	
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	168	48	0	
STRESS: TC COND. C -65C TO 150C, PRECONDITION 192 HR 30°C/60%RH, MSL3							
CY7C53150-AI (7C53150A)	2104858	610109389/90	TAIWN-G	300	50	0	
CY7C53150-AI (7C53150A)	2104858	610109389/90	TAIWN-G	500	50	0	
CY7C53150-AI (7C53150A)	2104858	610109389/90	TAIWN-G	1000	50	0	
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	300	48	0	
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	500	47	0	
CY7C53150-AI (7C53150B)	2110601	610115306	TAIWN-G	1000	47	0	
CY7C53150-AI (7C53150B)	2113874	340100180/1	TAIWN-G	300	48	0	
CY7C53150-AI (7C53150B)	2113874	340100180/1	TAIWN-G	500	48	0	
CY7C53150-AI (7C53150B)	2113874	340100180/1	TAIWN-G	1000	48	0	

Reliability Test Data

QTP #: 030702

<i>Device</i>	<i>Fab Lot #</i>	<i>Assembly Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
STRESS: ACOUSTIC							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	COMP	15	0	
CY8C27443 (8C27443A)	2324841	510305472	INDNS-0	COMP	15	0	
CY8C27443 (8C27443A)	2323812	510305917	INDNS-0	COMP	15	0	
STRESS: DATA RETENTION, PLASTIC, NO BIAS, 125C							
CY8C27443 (8C27443A)	2324841	510305472	INDNS-0	250	164	0	
CY8C27443 (8C27443A)	2324841	510305472	INDNS-0	500	164	0	
CY8C27443 (8C27443A)	2323812	510305917	INDNS-0	250	159	0	
CY8C27443 (8C27443A)	2323812	510305917	INDNS-0	500	159	0	
STRESS: ESD-CHARGE DEVICE MODEL, 500V							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	COMP	9	0	
STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2,200V							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	COMP	9	0	
STRESS: HI-ACCEL SATURATION TEST, 130C, 85%RH, 5.5V							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	128	45	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 125C, 5.75V, Vcc Max							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	96	822	0	
CY8C27443 (8C27443A)	2324841	510305472	INDNS-0	96	697	0	
CY8C27443 (8C27443A)	2323812	510305917	INDNS-0	96	700	0	
STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-LATENT FAILURE RATE, 125C, 5.75V, Vcc Max							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	200	593	0	
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	1000	593	0	
STRESS: PRESSURE COOKER TEST 121C, 100%RH							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	128	50	0	
STRESS: STATIC LATCH-UP TESTING, 125C, 12V, ±300mA							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	COMP	3	0	

Reliability Test Data

QTP #: 030702

<i>Device</i>	<i>Fab Lot #</i>	<i>Assembly Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
STRESS: TC COND. C -65C TO 150C							
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	300	50	0	
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	500	50	0	
CY8C27443 (8C27443A)	2315276	510304158	INDNS-0	1000	50	0	
CY8C27443 (8C27443A)	2324841	510305472	INDNS-0	300	50	0	
CY8C27443 (8C27443A)	2324841	510305472	INDNS-0	500	50	0	
CY8C27443 (8C27443A)	2324841	510305472	INDNS-0	1000	50	0	
CY8C27443 (8C27443A)	2323812	510305917	INDNS-0	300	50	0	
CY8C27443 (8C27443A)	2323812	510305917	INDNS-0	500	50	0	
CY8C27443 (8C27443A)	2323812	510305917	INDNS-0	1000	50	0	

Reliability Test Data

QTP #: 043105

<i>Device</i>	<i>Fab Lot #</i>	<i>Assembly Lot #</i>	<i>Assy Loc</i>	<i>Duration</i>	<i>Samp</i>	<i>Rej</i>	<i>Failure Mechanism</i>
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STRESS: ESD-CHARGE DEVICE MODEL, 500V

CY8C27443 (8C27443B)	2403330	510403166	INDNS-0	COMP	9	0	
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STRESS: ESD-HUMAN BODY CIRCUIT PER JESD22, METHOD A114-B, 2,200V

CY8C27443 (8C27443B)	2403330	510403166	INDNS-0	COMP	9	0	
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STRESS: ESD-HUMAN BODY CIRCUIT PER MIL STD 883, METHOD 3015, 2,200V

CY8C27443 (8C27443B)	2403330	510403166	INDNS-0	COMP	3	0	
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STRESS: HIGH TEMP DYNAMIC OPERATING LIFE-EARLY FAILURE RATE, 125C, 5.5V, Vcc Max

CY8C27443 (8C27443B)	2400030	610438921	INDNS-0	96	847	0	
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CY8C27443 (8C27443B)	2414285	610438918	INDNS-0	96	758	0	
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STRESS: PRESSURE COOKER TEST, 121C, 100%RH, PRE COND 168HRS 85C/85%RH, MSL1

CY8C27443 (8C27443B)	2400030	610438921	INDNS-0	96	85	0	
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CY8C27443 (8C27443B)	2400030	610438921	INDNS-0	168	85	0	
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STRESS: STATIC LATCH-UP TESTING, 125C, 11.1V, ±300mA

CY8C27443 (8C27443B)	2403330	510403166	INDNS-0	COMP	3	0	
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Reliability Test Data

QTP #: 074504

Device	Fab Lot #	Assembly Lot #	Assy Loc	Duration	Samp	Rej	Failure Mechanism
STRESS: ETEST YIELD							
CY8C27443 (8C27443B)	2739935			COMP		COMPARABLE	
STRESS: SORT YIELD							
CY8C27443 (8C27443B)	2739935			COMP		COMPARABLE	